

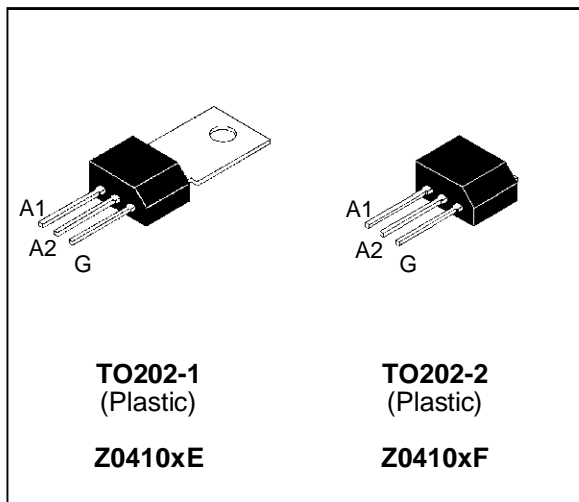
STANDARD TRIACS

FEATURES

- $I_{T(RMS)} = 4A$
- $V_{DRM} = 400V$ to $800V$
- $I_{GT} \leq 25mA$

DESCRIPTION

The Z0410xE/F series of triacs uses a high performance TOP GLASS PNPN technology. These parts are intended for general purpose switching and phase control applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	Z0410xE/F $T_c = 75^\circ C$	4	A
		Z0410xF $T_a = 25^\circ C$	0.95	
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = $25^\circ C$)	$t_p = 8.3$ ms	22	A
		$t_p = 10$ ms	20	
I^2t	I^2t Value for fusing	$t_p = 10$ ms	2	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 50$ mA $di_G/dt = 0.1$ A/ μs .	Repetitive F = 50 Hz	10	A/ μs
		Non Repetitive	50	
T_{stg} T_j	Storage and operating junction temperature range		- 40, + 150 - 40, + 125	$^\circ C$
TI	Maximum lead temperature for soldering during 10s at 4.5mm from case		260	$^\circ C$

Symbol	Parameter	Voltage				Unit
		D	M	S	N	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$	400	600	700	800	V

Z0410xE/F

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth(j-a)	Junction to ambient	Z0410xE	80	°C/W
		Z0410xF	100	
Rth(j-c)	Junction to case for D.C		10	°C/W
Rth(j-c)	Junction to case for A.C 360° conduction angle (F=50Hz)		7.5	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 0.2 \text{ W}$ $P_{GM} = 3 \text{ W}$ ($t_p = 20 \mu\text{s}$) $I_{GM} = 1.2 \text{ A}$ ($t_p = 20 \mu\text{s}$)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Sensitivity		Unit
						10	
I_{GT}	$V_D = 12\text{V (DC)}$	$R_L = 33\Omega$	$T_j = 25^\circ\text{C}$	I-II-III-IV	MAX	25	mA
V_{GT}	$V_D = 12\text{V (DC)}$	$R_L = 33\Omega$	$T_j = 25^\circ\text{C}$	I-II-III-IV	MAX	1.5	V
V_{GD}	$V_D = V_{DRM}$	$R_L = 3.3\text{k}\Omega$	$T_j = 125^\circ\text{C}$	I-II-III-IV	MIN	0.2	V
tgt	$V_D = V_{DRM}$	$I_G = 40\text{mA}$	$T_j = 25^\circ\text{C}$	I-II-III-IV	TYP	2	μs
		$I_T = 5.5\text{A}$					
		$di_G/dt = 0.5\text{A}/\mu\text{s}$					
I_H^*	$I_T = 50 \text{ mA}$	Gate open	$T_j = 25^\circ\text{C}$		MAX	25	mA
I_L	$I_G = 1.2 I_{GT}$		$T_j = 25^\circ\text{C}$	I-III-IV	TYP	25	mA
				II	TYP	50	
V_{TM}^*	$I_{TM} = 5.5\text{A}$	$t_p = 380\mu\text{s}$	$T_j = 25^\circ\text{C}$		MAX	2	V
I_{DRM} I_{RRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$		$T_j = 25^\circ\text{C}$		MAX	5	μA
			$T_j = 110^\circ\text{C}$		MAX	200	
dV/dt^*	$V_D = 67\% V_{DRM}$ Gate open		$T_j = 110^\circ\text{C}$		MIN	200	$\text{V}/\mu\text{s}$
					TYP	400	
$(dV/dt)_c^*$	$(di/dt)_c = 1.8 \text{ A/ms}$		$T_j = 110^\circ\text{C}$		MIN	5	$\text{V}/\mu\text{s}$

* For either polarity of electrode A_2 voltage with reference to electrode A_1

ORDERING INFORMATION

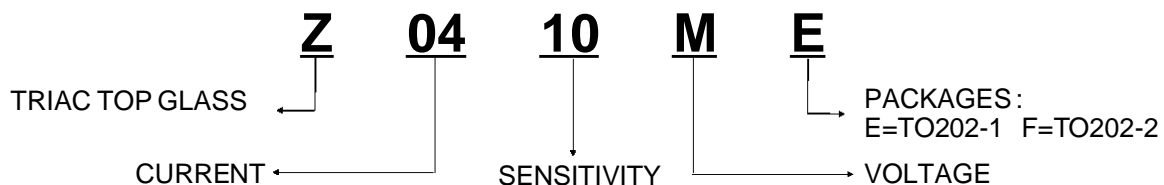


Fig.1 : Maximum RMS power dissipation versus RMS on-state current.

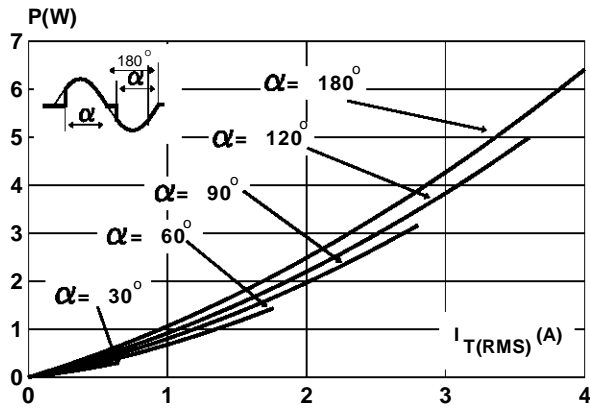


Fig.3 : Maximum RMS power dissipation versus RMS on-state current.

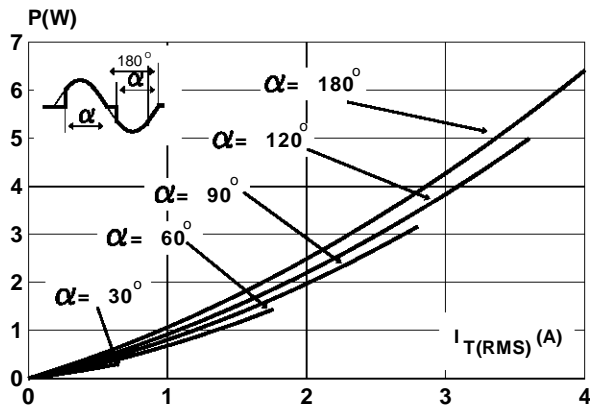


Fig.5 : RMS on-state current versus case temperature (TO202-1).

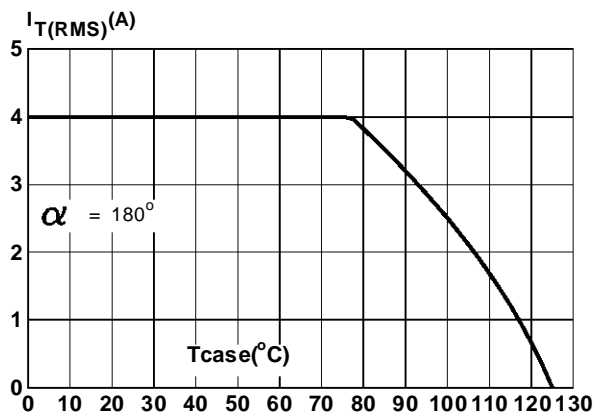


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperature (Tamb and Tcase) for different thermal resistances heatsink + contact (TO202-1).

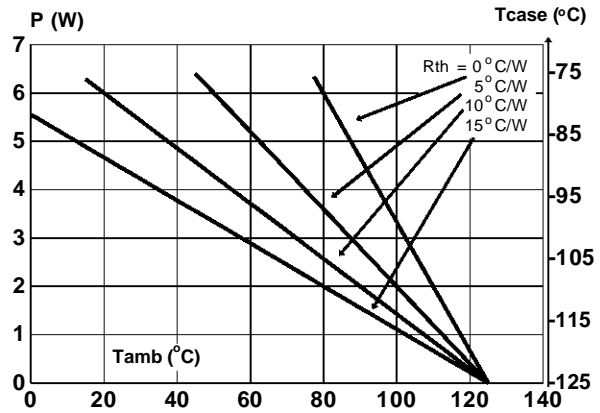


Fig.4 : Correlation between maximum RMS power dissipation and maximum allowable temperature (Tamb and Tcase) (TO202-2).

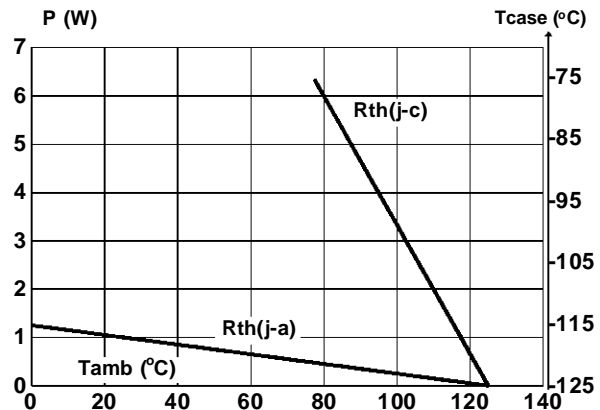


Fig.6 : RMS on-state current versus case temperature (TO202-2).

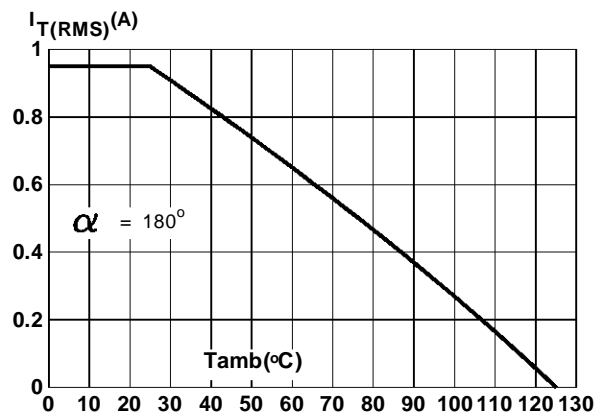


Fig.6 : Relative variation of thermal impedance versus pulse duration (TO202-1).

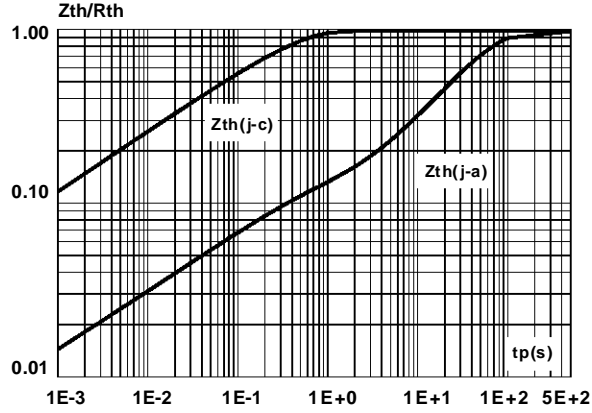


Fig.7 : Relative variation of thermal impedance junction to ambient versus pulse duration (TO202-2).

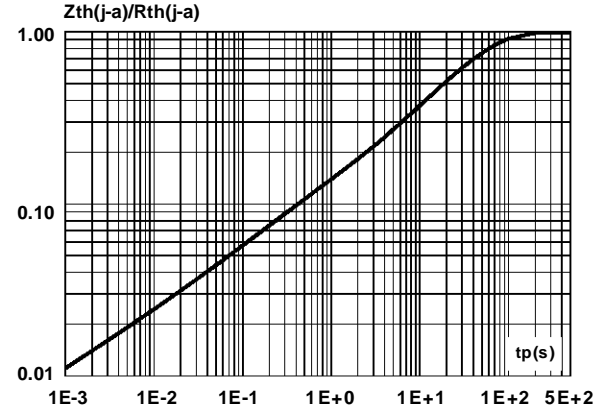


Fig.9 : Relative variation of gate trigger current and holding current versus junction temperature.

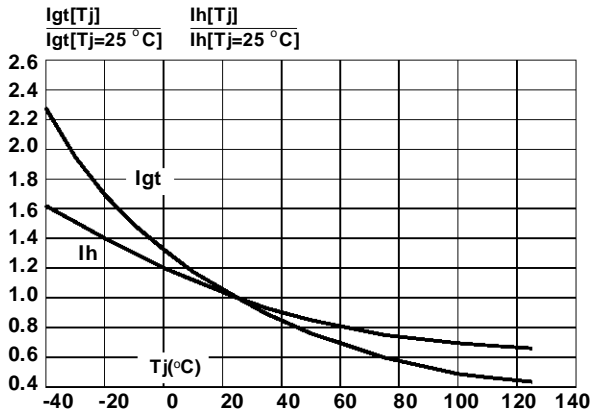


Fig.10 : Non repetitive surge peak on-state current versus number of cycles.

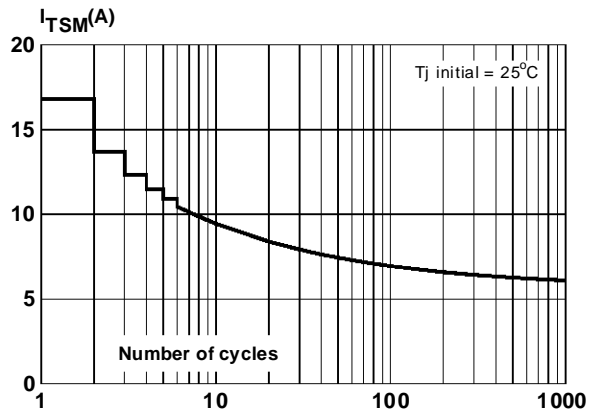


Fig.11 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $tp \leq 10ms$, and corresponding value of I^2t .

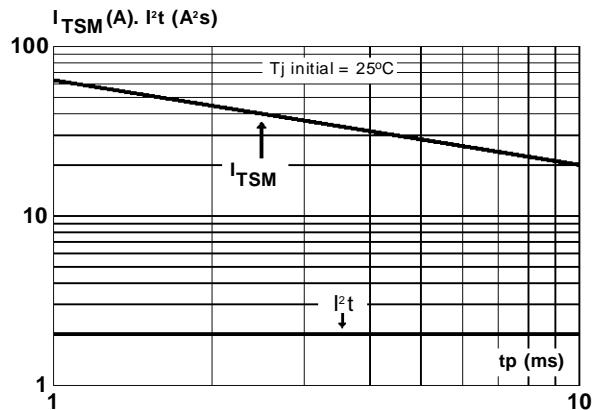
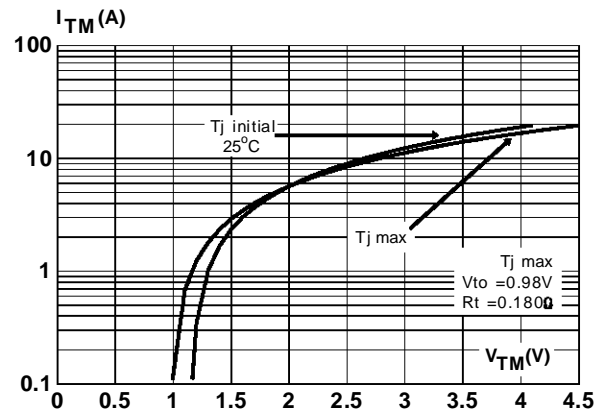


Fig.12 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA
TO202-1 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A			10.1			0.398
B	13.7			0.540		
C	7.3			0.287		
D	10.5			0.413		
F			1.5			0.059
G	3.2			0.126		
H	0.51			0.020		
I		3.16	3.20		0.124	0.126
J	1.5			0.059		
M	4.5			0.177		
N			5.3			0.209
N1	2.54			0.100		
O			1.4			0.055
P			0.7			0.028

Marking : type number
Weight : 1.4 g

Z0410xE/F

PACKAGE MECHANICAL DATA TO202-2 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A			10.1			0.398
B	1.2			0.047		
C	7.3			0.287		
D	10.5			0.413		
E	7.4			0.290		
F			1.5			0.059
H	0.51			0.020		
J	1.5			0.059		
M	4.5			0.177		
N			5.3			0.209
N1	2.54			0.100		
O			1.4			0.055
P			0.7			0.028

Marking : type number
Weight : 1.0 g

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